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SMD Schottky Barrier Diode

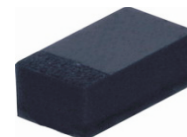


CDBUR0230

Io = 200 mA

VR = 30 Volts

RoHS Device

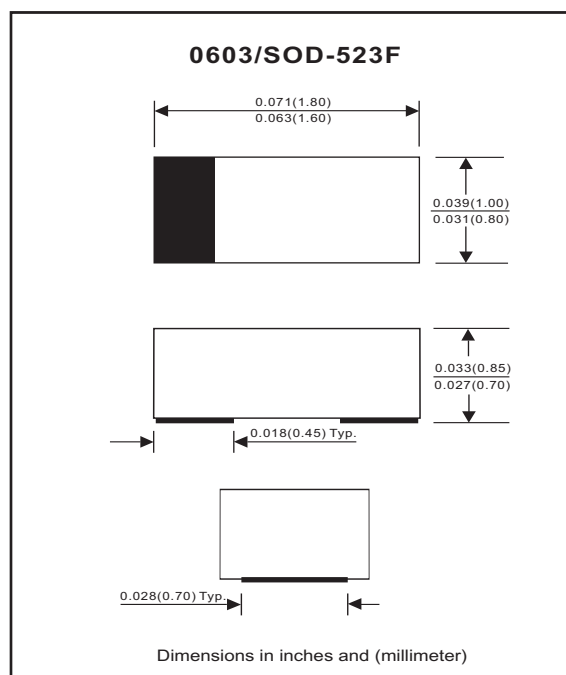


Features

- Designed for mounting on small surface.
- Extremely thin/leadless package.
- Low drop-down voltage.
- Majority carrier conduction.

Mechanical data

- Case: 0603/SOD-523F standard package, molded plastic.
- Terminals: Gold plated, solderable per MIL-STD-750, method 2026.
- Polarity: Indicated by cathode band.
- Mounting position: Any
- Weight: 0.003 gram(approx.).



Maximum Rating (at TA=25°C unless otherwise noted)

Parameter	Conditions	Symbol	Min	Typ	Max	Unit
Repetitive peak reverse voltage		VRRM			35	V
Reverse voltage		VR			30	V
Average forward current		Io			200	mA
Forward current,surge peak	8.3 ms single half sine-wave superimposed on rate load(JEDEC method)	IFSM		3000		mA
Power Dissipation		PD			150	mW
Storage temperature		TSTG	-40		+125	°C
Junction temperature		Tj			+125	°C

Electrical Characteristics (at TA=25°C unless otherwise noted)

Parameter	Conditions	Symbol	Min	Typ	Max	Unit
Forward voltage	IF = 200 mA DC	VF			0.50	V
Reverse current	VR = 30V	IR			30	uA
Capacitance between terminals	F = 1 MHz and 10 VDC reverse voltage	CT		9		pF

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RATING AND CHARACTERISTIC CURVES (CDBUR0230)

Fig. 1 - Forward characteristics

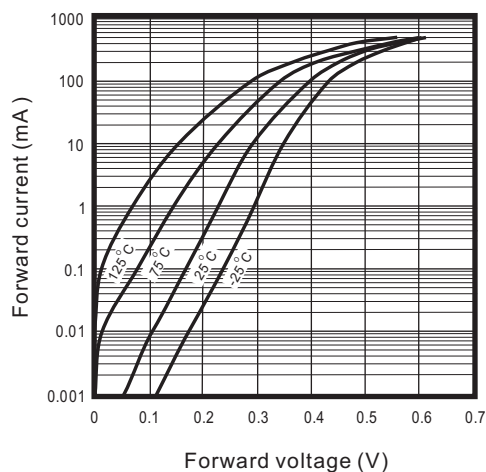


Fig. 2 - Reverse characteristics

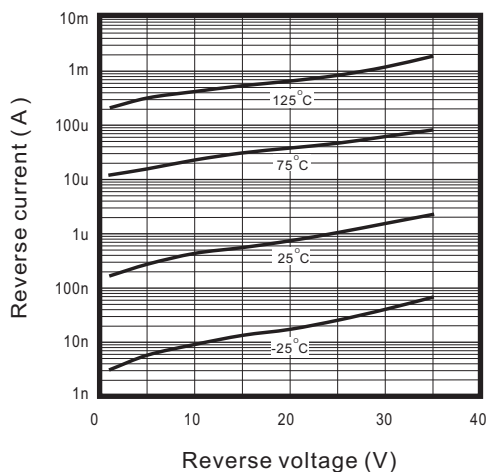


Fig.3 - Capacitance between terminals characteristics

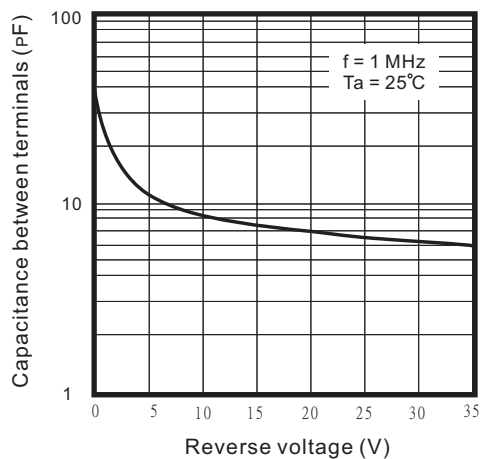


Fig.4 - Current derating curve

